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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	10/623794
	Filing Date	July 21, 2003
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2811 2823
	Examiner Name	Unknown Michelle Estrada
Sheet 1 of 11		Attorney Docket No: 1303.108US1

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	Examiner Name	Unknown M. Estrada
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
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1/10/05

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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